L	Hits	Search Text	DB	Time stamp
Number				
-	4	(("6069485") or ("5904490")).PN.	USPAT;	2003/12/04
			US-PGPUB;	11:22
			EPO; JPO; DERWENT;	
			IBM TDB	ŀ
1 -	2	("5610104").PN.	USPĀT;	2003/12/03
	_	, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	18:40
			EPO; JPO;	
			DERWENT;	
	23044		IBM_TDB	
-	23044	transistor near2 structure	USPAT;	2003/12/04
			US-PGPUB; EPO; JPO;	11:22
			DERWENT;	
ļ I			IBM TDB	
-	11021	transistor adj structure	USPAT;	2003/12/04
	1		US-PGPUB;	11:23
			EPO; JPO;	
			DERWENT;	
_	6868	(transistor ad) structure) and	IBM_TDB	2002/12/04
		257/\$.ccls.	USPAT; US-PGPUB;	2003/12/04
			EPO; JPO;	11.23
			DERWENT;	
			IBM_TDB	
-	118	(USPAT;	2003/12/04
		insulator	US-PGPUB;	11:24
			EPO; JPO; DERWENT;	
			IBM TDB	ĺ
-	13	((transistor adj structure) and	USPAT;	2003/12/04
		257/\$.ccls.) and ((base with gate with	US-PGPUB;	11:36
		drain) with insulator)	EPO; JPO;	
			DERWENT;	
	350	324/769.ccls.	IBM_TDB	0000/10/04
_	330	324/769.0013.	USPAT; US-PGPUB;	2003/12/04 11:36
			EPO; JPO;	11.30
			DERWENT;	
			IBM TDB	
-	4	324/769.ccls. and (determin\$4 near5	USPĀT;	2003/12/04
		capacitance) same (gate and source and	US-PGPUB;	12:54
		drain)	EPO; JPO;	}
]		DERWENT; IBM TDB	
_	4	("5304925" "5493231" "5493238"	USPAT	2003/12/04
		"5519336").PN.		11:45
-	3	("5194923" "5268318" "5600578").PN.	USPAT	2003/12/04
				12:54
-	371	(determin\$4 near5 capacitance) same (gate and source and drain)	USPAT;	2003/12/04
	i	and source and drain)	US-PGPUB; EPO; JPO;	13:05
			DERWENT;	
			IBM TDB	
- 1	14	((determin\$4 near5 capacitance) same	USPĀT;	2003/12/04
		(gate and source and drain)) and measur\$4	US-PGPUB;	12:55
		near5 characteristic	EPO; JPO;	
			DERWENT;	
_	4	((determin\$4 near5 capacitance) same	IBM_TDB USPAT;	2003/12/04
	*	(gate and source and drain)) and	US-PGPUB;	13:01
		324/766-769.ccls.	EPO; JPO;	
]			DERWENT;	
			IBM_TDB	
-	356	((determin\$4 near5 capacitance) same	USPAT;	2003/12/04
		(gate and source and drain)) and (transistor or integrated)	US-PGPUB;	13:06
]	(cransiscor or integrated)	EPO; JPO; DERWENT;	
	ĺ		IBM TDB	
		<u> </u>		L.,

1 -				1 0000 110 10
	95	(((determin\$4 near5 capacitance) same (gate and source and drain)) and (transistor or integrated)) and (bias adj voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/04 13:37
-	12	(measur\$4 near5 capacitance near5 (transistor or (integrated adj circuit)))	IBM_TDB USPAT; US-PGPUB;	2003/12/04 13:39
		and 324/766-769.ccls.	EPO; JPO; DERWENT; IBM TDB	
-	186	measur\$4 near5 capacitance near5 (transistor or (integrated adj circuit))	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/04
_	0	("406085019").PN.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/12/04 16:13
-	9943	Aizawa.inv.	DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/12/04 16:14
_	0	Aizawa.inv. and "406085019"	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/12/04
		7: inv 1000050101	EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/12/04
_	1	Aizawa.inv. and "06085019"	US-PGPUB; EPO; JPO; DERWENT;	16:17
-	2	("6207477").PN.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/04 16:17
-	186	measur\$4 near5 capacitance near5 (transistor or (integrated adj circuit))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/04 18:38
-	781	measur\$4 near5 capacitance same (transistor or (integrated adj circuit))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/05 11:29
-	52	(measur\$4 near5 capacitance same (transistor or (integrated adj circuit))) and (word or bit) adj line	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/04 18:39
-	2261	memory adj array adj2 cell	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/05 11:30
-	781	measur\$4 near5 capacitance same (transistor or (integrated adj circuit))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/05 11:29
-	0	<pre>(memory adj array adj2 cell) and (measur\$4 near5 capacitance same (transistor or (integrated adj circuit)))</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/05 11:29

Search History 12/5/03 2·43·25 PM Page 2

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-	78	(memory adj array adj2 cell) and	USPAT;	2003/12/05
		(measur\$4 or determin\$4) with capacitance	US-PGPUB;	11:34
			EPO; JPO;	
			DERWENT;	
ĺ			IBM TDB	
-	50	((memory adj array adj2 cell) and	USPAT;	2003/12/05
		(measur\$4 or determin\$4) with	US-PGPUB;	13:37
		capacitance) and (word adj line) and (bit	EPO; JPO;	
		adj line)	DERWENT;	
	ļ		IBM_TDB	
-	17	(("3,753,373") or ("4,473,796") or	USPAT;	2003/12/05
		("4,498,044") or ("5,416,470") or	US-PGPUB;] 13:38
		("5,701,101") or ("5,808,516") or	EPO; JPO;	
		("5,886,529") or ("5,986,456") or	DERWENT;	
		("6,054,867")).PN.	IBM TDB	